

Attached is a set of rewritten Claims in accordance with amendments made herein.

Kindly enter the following amendments:

IN THE CLAIMS:

Please amend the Claims as follows:

10. (Twice Amended) A stripping method which comprises stripping a resist film [and/or an etching residue] on a semiconductor wafer having an exposed metal film, by using a stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine [or an alkanolamine], (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components.

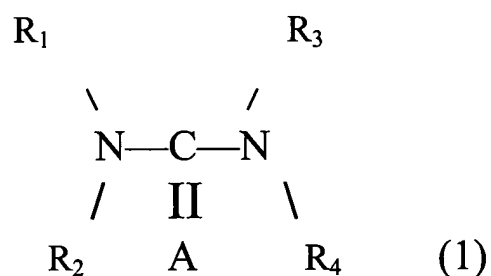
11. (Twice Amended) A stripping method which comprises stripping a resist film [and/or an etching residue] on a semiconductor wafer having an exposed metal film, by using a stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine [or an alkanolamine], (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components,

wherein the amounts of the components (a), (b), (c) and (d) are 1 to 60% by mass, 0.1 to 20% by mass, 5 to 70% by mass and 2 to 40% by mass, respectively.

12. (Twice Amended) A stripping method which comprises stripping a resist film [and/or an etching residue] on a semiconductor wafer having an exposed metal film, by using a stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (a) is a compound represented by the following general formula

(1):



(R₁, R₂, R₃ and R₄ are each independently a hydrogen atom or an alkyl group having 1 to 3 carbon atoms; and A is an oxygen atom or a sulfur atom).

13. (Twice Amended) A stripping method which comprises stripping a resist film [and/or an etching residue] on a semiconductor wafer having an exposed metal film, by using a stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, having a benzene derivative having at least two phenolic hydroxyl groups in the molecule, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components.

14. (Twice Amended) A stripping method which comprises stripping a resist film [and/or an etching residue] on a semiconductor wafer having an exposed metal film, by using a stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (b) is a benzene derivative having at least two phenolic hydroxyl groups in the molecule having at least one compound selected from the group consisting of pyrogallol, hydroxyhydroquinone, fluoroglucinol, gallic acid and tannic acid.